



IPP041N12N3 G Information



For Reference Only

Part Number IPP041N12N3 G
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 120V 120A TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IPP041N12N3 G Specifications

Manufacturer Part Number	IPP041N12N3 G
Manufacturer	Infineon Technologies
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-220-3
Series	OptiMOS?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	120V
Current - Continuous Drain (Id) @ 25°C	120A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	4V @ 270μA
Gate Charge (Qg) (Max) @ Vgs	211nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	13800pF @ 60V
Vgs (Max)	±20V
FET Feature	-
Power Dissipation (Max)	300W (Tc)
Rds On (Max) @ Id, Vgs	4.1 mOhm @ 100A, 10V
Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	PG-TO-220-3
Package / Case	TO-220-3
	Report errors?

IPP041N12N3 G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP041N12N3 G Payment Methods

































If you have any question about IPP041N12N3 G, please do not hesitate to contact us!

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